

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Krueger, et al.

Examiner: Unknown

Serial No: 10/069,262

Art Unit: Unknown

For: LAYER STRUCTURE FOR BIPOLAR TRANSISTORS AND PROCESS
FOR THE PRODUCTION THEREOF

Filed: 22 February 2002

Date: 20 May 2002

Commissioner of Patents and Trademarks
Washington, D.C. 20231

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Under 37 CFR 1.97

This Information Disclosure Statement is filed with the missing parts of a national stage entry of a PCT application, so it is timely filed without payment of a fee. 37 CFR §1.97(b).

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made (37 CFR §1.56(g)), an admission that the information cited is, or is considered to be, material to patentability or that no other material information exists.

The filing of this Information Disclosure Statement shall not be construed as an admission against interest in any manner. Notice of January 9, 1992, 1135 O.G. 13, at 25.

This Information Disclosure Statement is made to comply with the duty of candor imposed on all individuals associated with the filing or prosecution of this application, as defined by 37 CFR §1.56(c).

Eight (8) U.S. patents, six (6) foreign patent documents and nine (9) non-patent

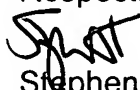
references are listed on the attached one (1) sheet of Form PTO/SB/08A and one (1) sheet of Form PTO/SB/08B which are made a part hereof. A copy of each is enclosed. Also enclosed in the filing papers, but not listed on the form, is a copy of a search report, dated 16 March 2000, from the German Patent Office on German application 199 40 278.7, which is the parent of the PCT application from which this US application is a national stage entry. Each of the references cited in this IDS is either directly cited in the German search report or is an English language equivalent of one of the citations in the search report.

Reference EC is in German, but Reference DF is an English language equivalent. Reference EE is also in German, but Reference DA is an English language equivalent. Reference EF is in German and there is no known English language equivalent.

References FC and FE are publications authored by employees of the applicant, the corporate name being translated into English as "Institute for Semiconductor Physics."

The foregoing Information Disclosure Statement is based upon the information known to the inventor or contained in the undersigned attorney's file as of the filing date of this statement and is inclusive of the best information known to each of the undersigned at that date. Prompt consideration of the Information Disclosure Statement and the references by the Examiner is earnestly requested.

Respectfully submitted,



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